Number of Lecture Hours/Week04I	IA Marks Exam Marks	
Lecture Hours/Week Total Number of 50 (10 Hours per Module) Lecture Hours CREDITS - 04 CREDITS - 04 Course objectives: This course will enable students to: • Explain various BJT parameters, connections and configurat • Explain construction and characteristics of JFETs and MOS • Explain various types of FET biasing, and demonstrate the u • Construct frequency response of BJT and FET amplifiers at u • Construct Feedback and Oscillator circuits using FET. Modules Module -1 BJT AC Analysis: BJT Transistor Modeling, The re transist Common emitter fixed bias, Voltage divider bias, Emitter configuration. Darlington connection-DC bias; The Hybrid e model, Approximate Hybrid Equivalent Circuit- Fixed bias divider, Emitter follower configuration; Complete Hybrid e model, Hybrid π Model. Module -2 Field Effect Transistors: Construction and Characteristics of Transfer Characteristics, Depletion type MOSFET, Enhancen MOSFET. FET Amplifiers: JFET small signal model, Fixed bias configuration, Voltage divider configuration, Comm configuration, Source-Follower Configuration, Cascade configuration	Exam Marks	20
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Module -3		L1, L2, L3
	ement type ration, Self mon Gate	
BJT and JFET Frequency Response: Logarithms, Decili frequency response – BJT Amplifier with RL, Low frequency is FET Amplifier, Miller effect capacitance, High frequency respon Amplifier, High frequency response-FET Amplifier, Multistage F Effects. Module -4	ement type ration, Self mon Gate	

Feedback and Oscillator Circuits: Feedback concepts, Feedback connection types, Practical feedback circuits, Oscillator operation, FET Phase shift oscillator, Wien bridge oscillator, Tuned Oscillator circuit, Crystal oscillator, UJT construction, UJT Oscillator.	L1,L2, L3
Module -5	
Power Amplifiers: Definition and amplifier types, Series fed class A	
amplifier, Transformer coupled class A amplifier, Class B amplifier	L1, L2, L3
operation and circuits, Amplifier distortion, Class C and Class D	
amplifiers. Voltage Regulators: Discrete transistor voltage regulation -	
Series and Shunt Voltage regulators.	
Course Outcomes: After studying this course, students will be able to:	

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- Describe the working principle and characteristics of BJT, FET, Single stage, cascaded and feedback amplifiers.
- Describe the Phase shift, Wien bridge, tuned and crystal oscillators using BJT/FET/UJT.
- Calculate the AC gain and impedance for BJT using re and h parameters models for CE and CC configuration.
- Determine the performance characteristics and parameters of BJT and FET amplifier using small signal model.
- Determine the parameters which affect the low frequency and high frequency responses of BJT and FET amplifiers and draw the characteristics.
- Evaluate the efficiency of Class A and Class B power amplifiers and voltage regulators.

Question paper pattern:

- The question paper will have ten questions.
- Each full question consists of 16 marks.
- There will be 2 full questions (with a maximum of Three sub questions) from each module.
- Each full question will have sub questions covering all the topics under a module. The students will have to answer 5 full questions, selecting one full question from each module.

Text Book:

Robert L. Boylestad and Louis Nashelsky, "Electronics devices and Circuit theory", Pearson, 10th/11th Edition, 2012, ISBN:978-81-317-6459-6.

Reference Books:

- 1. Adel S. Sedra and Kenneth C. Smith, "Micro Electronic Circuits Theory and Application", 5th Edition ISBN:0198062257
- 2. Fundamentals of Microelectronics, Behzad Razavi, John Weily ISBN 2013 978-81-265-2307-8
- 3. J.Millman & C.C.Halkias–Integrated Electronics, 2nd edition, 2010, TMH. ISBN 0-07-462245-5
- **4.** K. A. Navas, "Electronics Lab Manual", Volume I, PHI, 5th Edition, 2015, ISBN:9788120351424.